

PRELIMINARY
 Notice : This is not a final specification
 Some parametric limits are subject to change.

MITSUBISHI SEMICONDUCTOR <GaAs FET>

MGFS45V2527

2.5~2.7GHz BAND 30W INTERNALLY MATCHED GaAs FET

DESCRIPTION

The MGFS45V2527 is an internally impedance matched GaAs power FET especially designed for use in 2.5~2.7 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

- Class A operation
- Internally matched to 50 () system
- High output power
 $P_{1dB}=30W$ (TYP.) @ $f=2.5\sim 2.7GHz$
- High power gain
 $GLP=12dB$ (TYP.) @ $f=2.5\sim 2.7GHz$
- High power added efficiency
 $add=45\%$ (TYP.) @ $f=2.5\sim 2.7GHz$
- Low distortion [item -51]
 $IM3=-45dBc$ (TYP.) @ $P_o=34.5dBm$ S.C.L.

APPLICATION

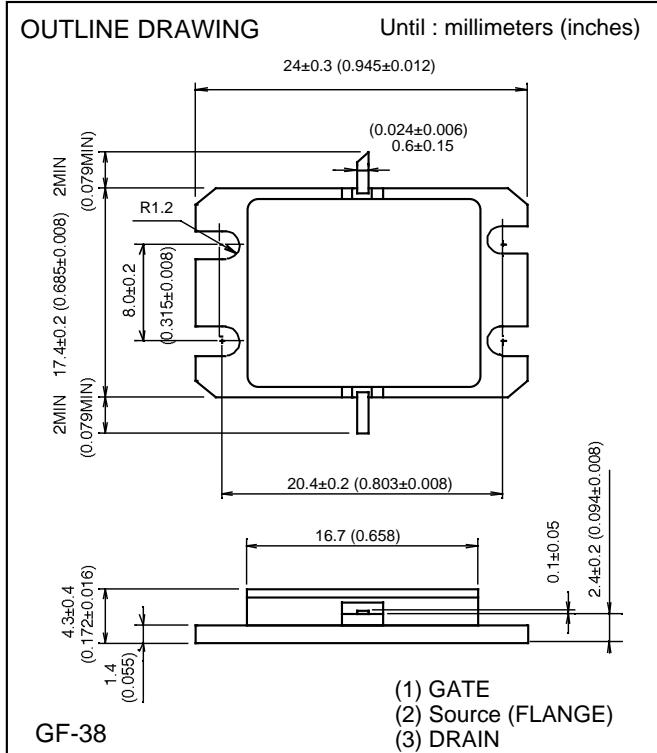
- item 01 : 2.5~2.7GHz band power amplifier
- item 51 : 2.5~2.7GHz band digital radio communication

QUALITY GRADE

- IG

RECOMMENDED BIAS CONDITIONS

- $V_{DS}=10V$
- $I_D=6.5A$
- $R_G=25$



ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Symbol	Parameter	Ratings	Unit
VGDO	Gate to drain voltage	-15	V
VGSO	Gate to source voltage	-15	V
ID	Drain current	22	A
IGR	Reverse gate current	-61	mA
IGF	Forward gate current	76	mA
PT	Total power dissipation *1	88	W
Tch	Channel temperature	175	°C
Tstg	Storage temperature	-65 ~ +175	°C

*1 : Tc=25°C

< Keep safety first in your circuit designs! >

Mitsubishi Electric Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage. Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of non-flammable material or (iii) prevention against any malfunction or mishap.

ELECTRICAL CHARACTERISTICS (Ta=25°C)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max	
VGS (off)	Saturated drain current	$V_{DS}=3V, I_D=60mA$	—	—	-5	V
P_{1dB}	Output power at 1dB gain compression	$V_{DS}=10V, I_D(RF\ off)=6.5A, f=2.5\sim 2.7GHz$	44	45	—	dBm
GLP	Linear power gain		11	12	—	dB
ID	Drain current		—	7.5	—	A
add	Power added efficiency		—	45	—	%
IM3	3rd order IM distortion *2		-42	-45	—	dBc
Rth (ch-c)	Thermal resistance *1	Vf method	—	—	1.7	°C/W

*1 : Channel to case

*2 : item -51, 2 tone test, $P_o=34.5dBm$ Single Carrier Level, $f=2.5, 2.6, 2.7GHz, f=5MHz$

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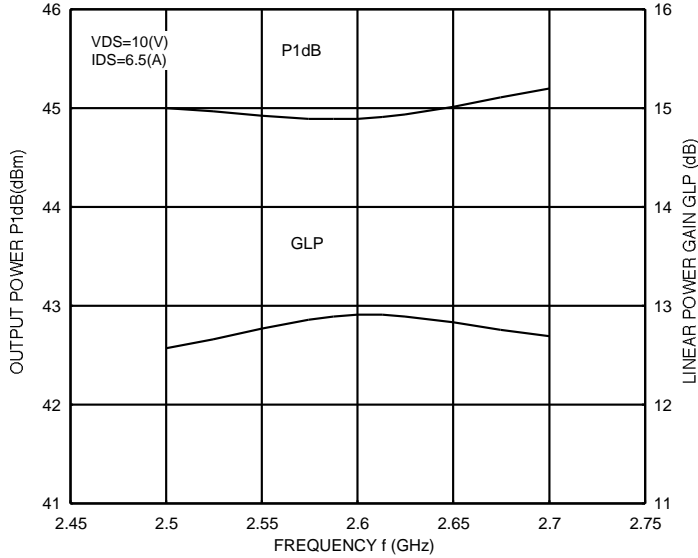
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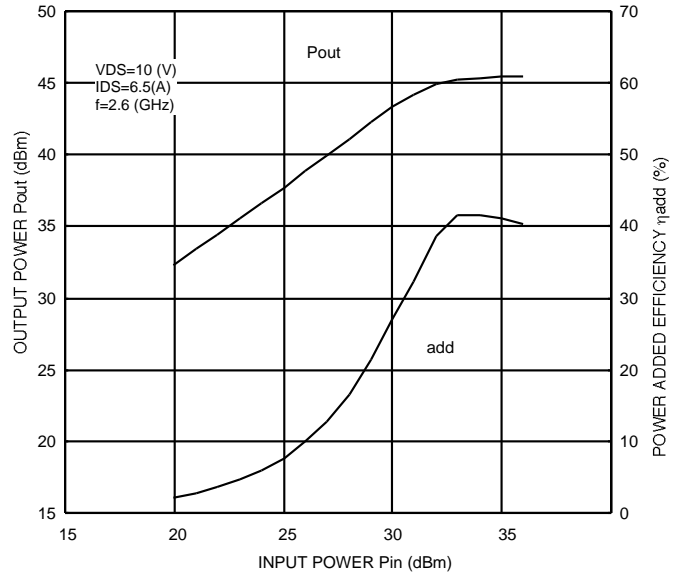
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TYPICAL CHARACTERISTICS

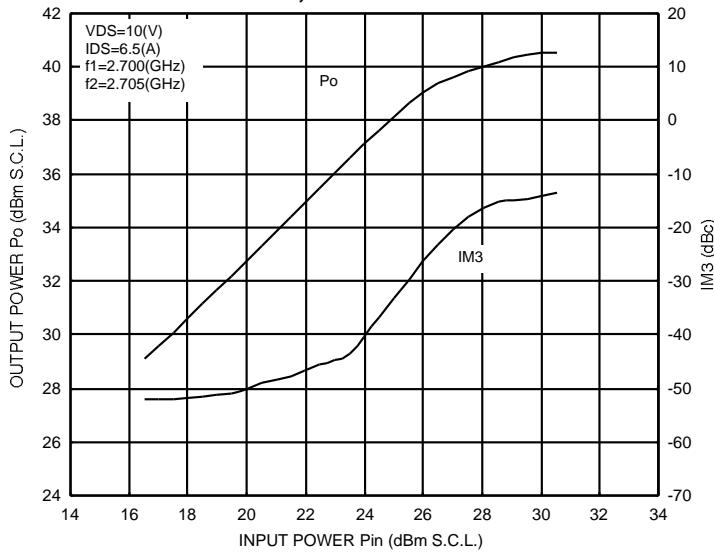
P1dB, GLP vs. f



Po, add vs. Pin



Po, IM3 vs. Pin



S Parameters (Tc=25°C, VDS=10V, IDS=6.5A)

f (GHz)	S-Parameter (TYP.)							
	S11		S21		S12		S22	
	Magn.	Angle(deg)	Magn.	Angle(deg)	Magn.	Angle(deg)	Magn.	Angle(deg)
2.40	0.57	165	4.25	50	0.03	15	0.15	-24
2.45	0.54	152	4.35	36	0.04	0	0.13	-37
2.50	0.52	138	4.40	21	0.04	-21	0.12	-60
2.55	0.45	123	4.49	6	0.04	-35	0.12	-82
2.60	0.39	106	4.60	-10	0.04	-60	0.12	-111
2.65	0.30	82	4.68	-28	0.04	-73	0.13	-134
2.70	0.19	37	4.68	-47	0.04	-89	0.12	-156
2.75	0.18	-25	4.57	-66	0.05	-117	0.13	176
2.80	0.30	-73	4.29	-86	0.04	-133	0.10	160